

filling in the cavities with a dielectric material to insulate the stud from a rest of the substrate and to integrate the stud with the substrate;

hollowing the front face of the substrate opposite each stud so as to make each stud show through and thus convert each stud into a conducting through-connection; and

physically forming points of contact opposite each face of each stud showing through by depositing a conducting material, insulated from the substrate, on each of these faces.

12. (New) The method of fabricating conducting through-connections between the front face and the rear face of a substrate as claimed in claim 11, wherein the filling of the cavities comprises:

depositing the dielectric material in the cavities; and

removing, from a surface of the substrate, overflows of the deposit of dielectric material by thinning the rear face of the substrate until the studs are uncovered.

13. (New) The method of fabricating conducting through-connections between the front face and the rear face of a substrate as claimed in claim 11, further comprising, after delimiting the studs and before filling in the cavities:

metallizing the studs by depositing a conducting layer on the studs.

14. (New) The method of fabricating conducting through-connections between the front face and the rear face of a substrate as claimed in claim 13, wherein the filling-in of the cavities comprises:

depositing the dielectric material in the cavities;

removing, from a surface of the substrate, overflows of the deposit of the dielectric material by thinning the rear face of the substrate until the studs are uncovered; and

removing the conducting layer from the surface of the substrate, by thinning of the metallized faces of the substrate.

15. (New) The method of fabricating conducting through-connections between the front face and the rear face of a substrate as claimed in claim 11, further comprising:

thinning the substrate until the dielectric material contained in the cavities is uncovered so as to make the studs show through on the front face of the substrate.

16. (New) The method of fabricating conducting through-connections between the front face and the rear face of a substrate as claimed in claim 11, further comprising:

hollowing the front face of the substrate opposite each stud until the dielectric material contained in the cavities is reached, so as to make the studs show through on the front face of the substrate.

17. (New) The method of fabricating conducting through-connections between the front face and the rear face of a substrate as claimed in claim 11, wherein the physical formation of the points of contact comprises:

depositing an insulating layer on a same side as the faces of the studs showing through;

opening up a contact region opposite each face of the studs showing through by masking and etching of the insulating layer;

depositing a conducting layer on the same side as the faces of the studs showing through; and

cutting out the points of contact by masking and etching of the conducting layer.

18. (New) The method of fabricating conducting through-connections between the front face and the rear face of a substrate as claimed in claim 11, wherein the dielectric filling material is glass.

19. (New) A substrate of silicon equipped with conducting through-connections between its front face and its rear face, wherein the conducting through-connections are silicon studs extending over an entire height of the substrate and are surrounded by a